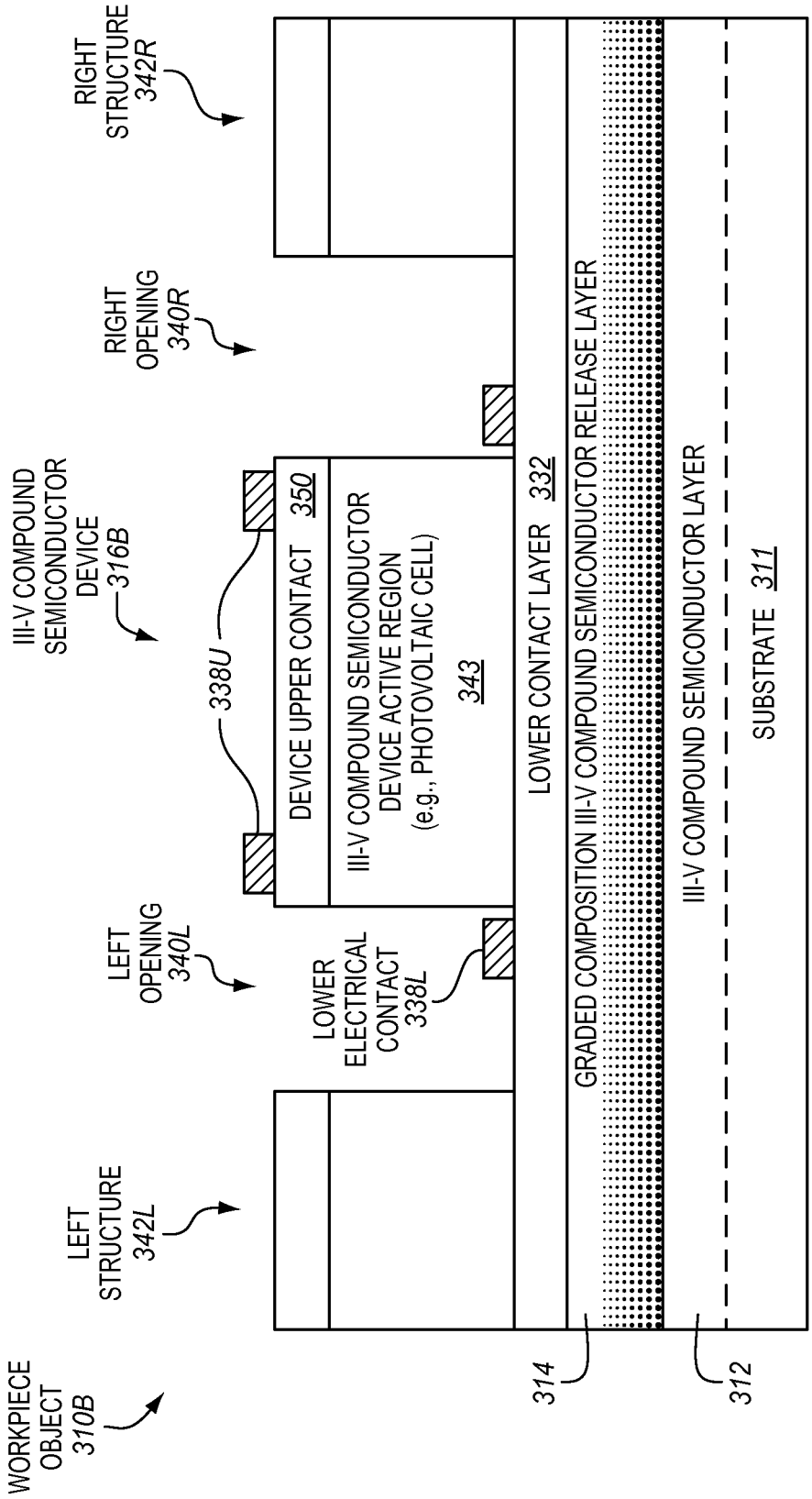
RIGHT STRUCTURE 342R
RIGHT OPENING 340R
III-V COMPOUND SEMICONDUCTOR DEVICE 316B
338U
DEVICE UPPER CONTACT 350
III-V COMPOUND SEMICONDUCTOR DEVICE ACTIVE REGION (e.g., PHOTOVOLTAIC CELL) 343
LOWER CONTACT LAYER 332
GRADED COMPOSITION III-V COMPOUND SEMICONDUCTOR RELEASE LAYER
III-V COMPOUND SEMICONDUCTOR LAYER
SUBSTRATE 311
LEFT OPENING 340L
LOWER ELECTRICAL CONTACT 338L
LEFT STRUCTURE 342L
WORKPIECE OBJECT 310B
314
312

FIG. 3B